



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D $T_A = +25^\circ\text{C}$
60V	85m Ω @ $V_{GS} = 10\text{V}$	4.1A
	110m Ω @ $V_{GS} = 4.5\text{V}$	3.6A

Features and Benefits

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed

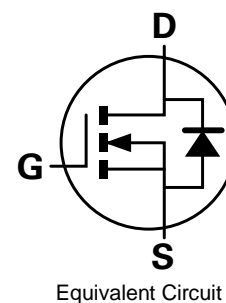
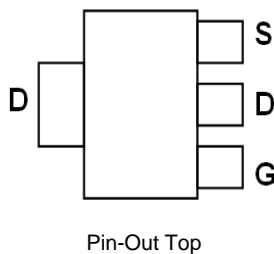
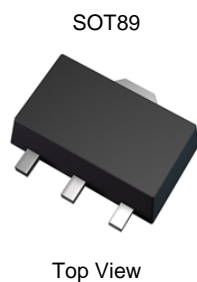
Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- DC-DC converters
- Power-management functions
- Backlighting

Mechanical Data

- Package: SOT89
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Finish Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208③
- Weight: 0.052 grams (Approximate)



Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	± 20	V
Continuous Drain Current (Note 6) $V_{GS} = 10\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	I_D	4.1	A
		$T_A = +70^\circ\text{C}$		3.3	
Pulsed Drain Current (10 μs Pulse, Duty Cycle $\leq 1\%$)			I_{DM}	15	A
Maximum Body Diode Continuous Current (Note 6)			I_S	2.5	A
Pulsed Body Diode Current (10 μs Pulse, Duty Cycle $\leq 1\%$)			I_{SM}	15	A
Avalanche Current, $L = 0.1\text{mH}$ (Note 7)			I_{AS}	11	A
Avalanche Energy, $L = 0.1\text{mH}$ (Note 7)			E_{AS}	6	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^\circ\text{C}$	P_D	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State $t < 10\text{s}$	$R_{\theta JA}$	122	$^\circ\text{C/W}$
			72	$^\circ\text{C/W}$
Total Power Dissipation (Note 6)	$T_A = +25^\circ\text{C}$	P_D	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State $t < 10\text{s}$	$R_{\theta JA}$	58	$^\circ\text{C/W}$
			34	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	12	$^\circ\text{C/W}$
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 16\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	—	3.0	V	$I_D = 250\mu\text{A}, V_{DS} = V_{GS}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	70	85	m Ω	$V_{GS} = 10\text{V}, I_D = 2.5\text{A}$
			76	110		$V_{GS} = 4.5\text{V}, I_D = 1.5\text{A}$
Diode Forward Voltage	V_{SD}	—	0.75	1.2	V	$I_S = 12\text{A}, V_{GS} = 0\text{V}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	588	—	pF	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$ $F = 1\text{MHz}$
Output Capacitance	C_{oss}	—	26.5	—		
Reverse Transfer Capacitance	C_{rss}	—	20	—		
Gate Resistance	R_g	—	1.5	—	Ω	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$,
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	5.6	—	nC	$V_{DS} = 30\text{V}, I_D = 3\text{A}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	12.3	—		
Gate-Source Charge	Q_{gs}	—	1.7	—		
Gate-Drain Charge	Q_{gd}	—	1.9	—		
Turn-On Delay Time	$t_{D(ON)}$	—	3.5	—	ns	$V_{DD} = 30\text{V}, V_{GS} = 10\text{V}$ $R_L \cong 50\Omega, R_g \cong 20\Omega$
Turn-On Rise Time	t_R	—	4.1	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	35	—		
Turn-Off Fall Time	t_F	—	11	—		
Body Diode Reverse Recovery Time	t_{RR}	—	18	—	ns	$I_S = 12\text{A}, di/dt = 100\text{A}/\mu\text{s}$
Body Diode Reverse Recovery Charge	Q_{RR}	—	12	—	nC	$I_S = 12\text{A}, di/dt = 100\text{A}/\mu\text{s}$

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1 inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^\circ\text{C}$.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

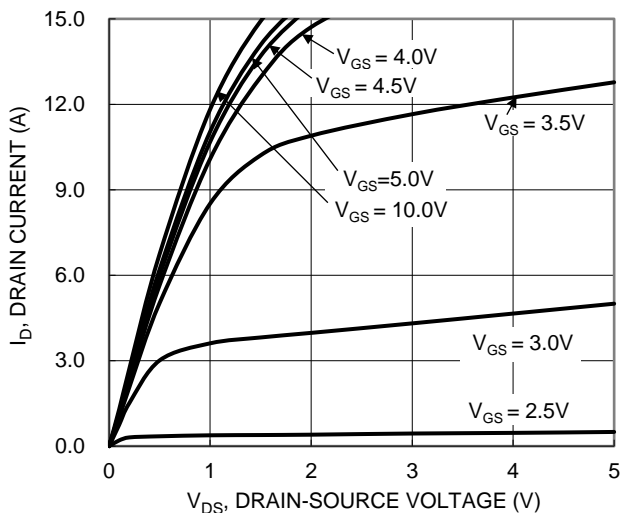


Figure 1. Typical Output Characteristic

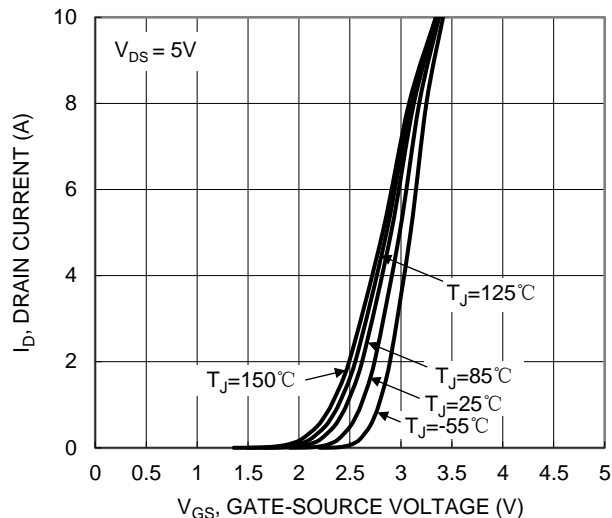


Figure 2. Typical Transfer Characteristic

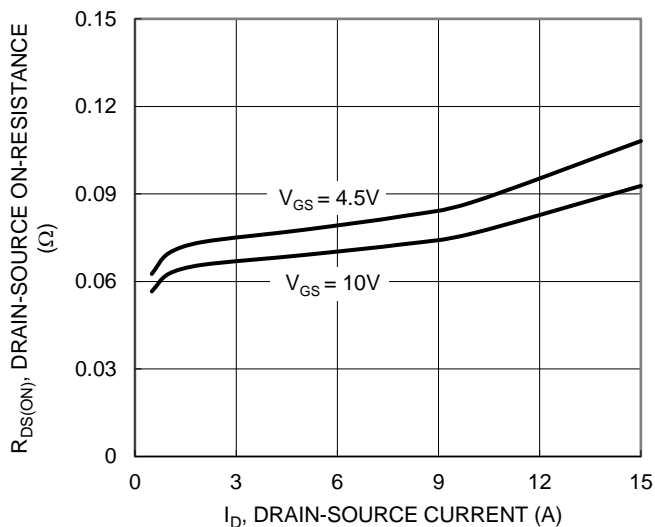


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

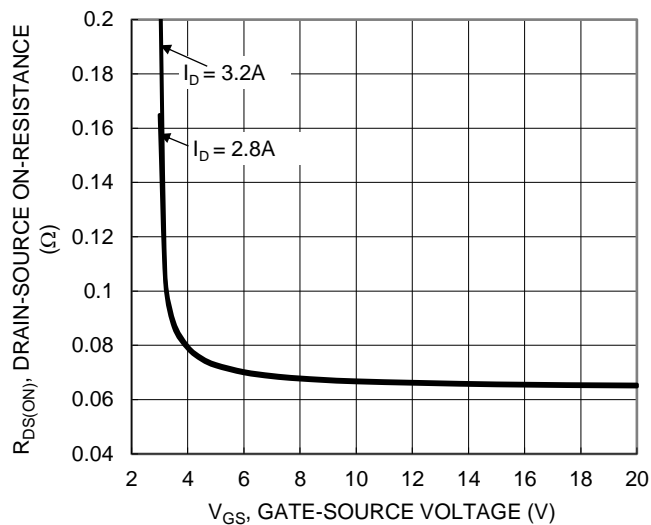


Figure 4. Typical Transfer Characteristic

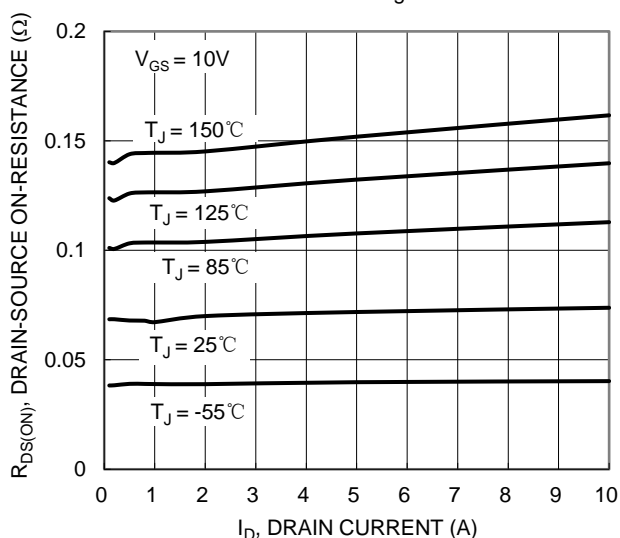


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

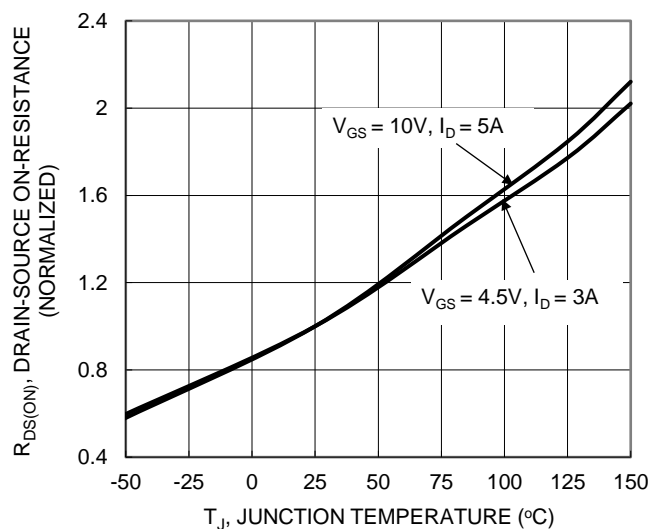


Figure 6. On-Resistance Variation with Temperature

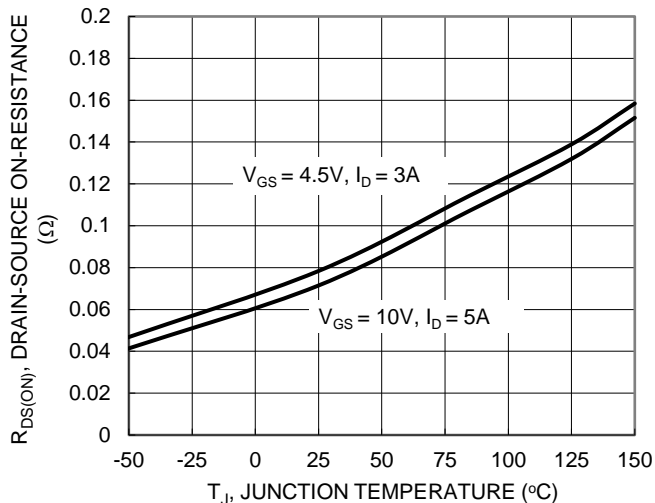


Figure 7. On-Resistance Variation with Temperature

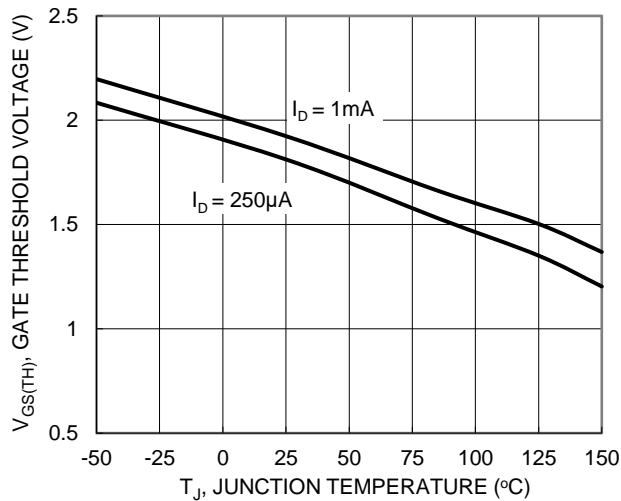


Figure 8. Gate Threshold Variation vs. Junction Temperature

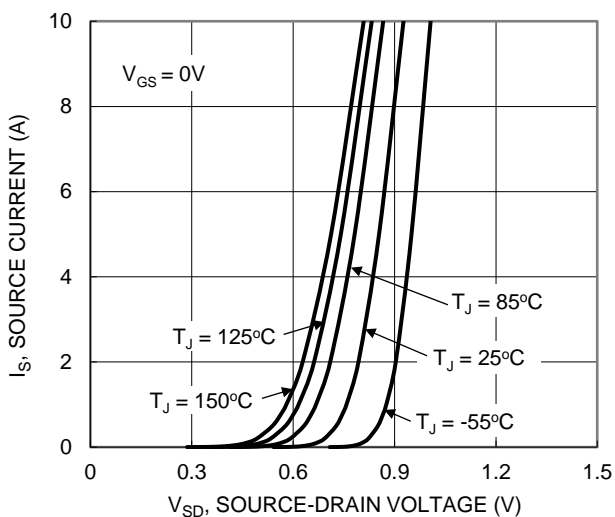


Figure 9. Diode Forward Voltage vs. Current

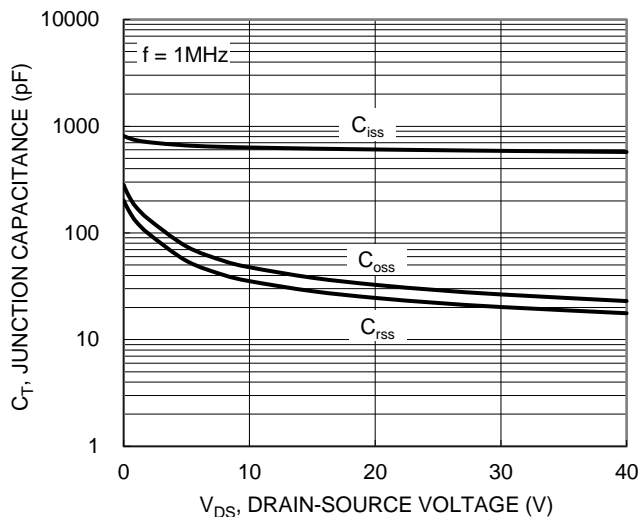


Figure 10. Typical Junction Capacitance

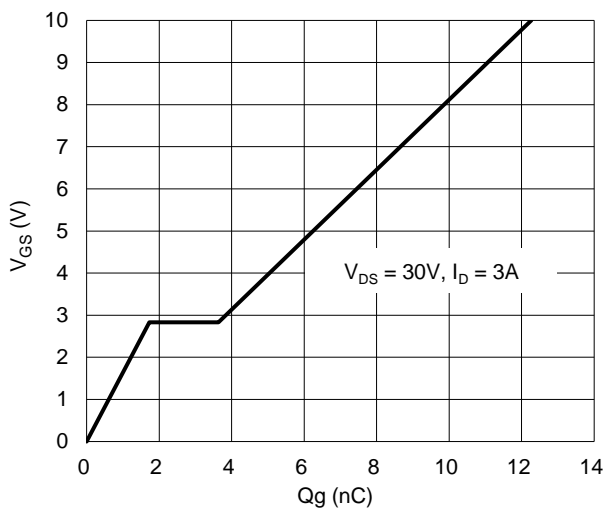


Figure 11. Gate Charge

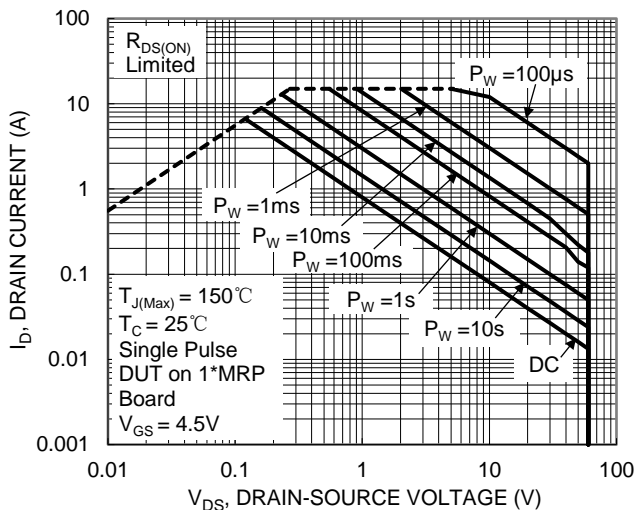


Figure 12. SOA, Safe Operation Area

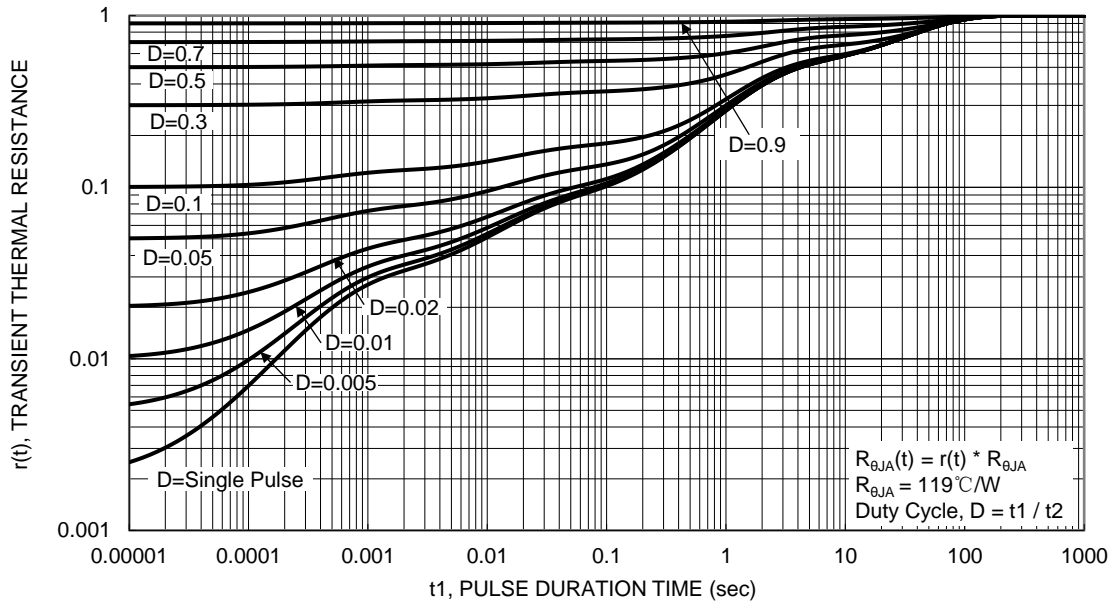
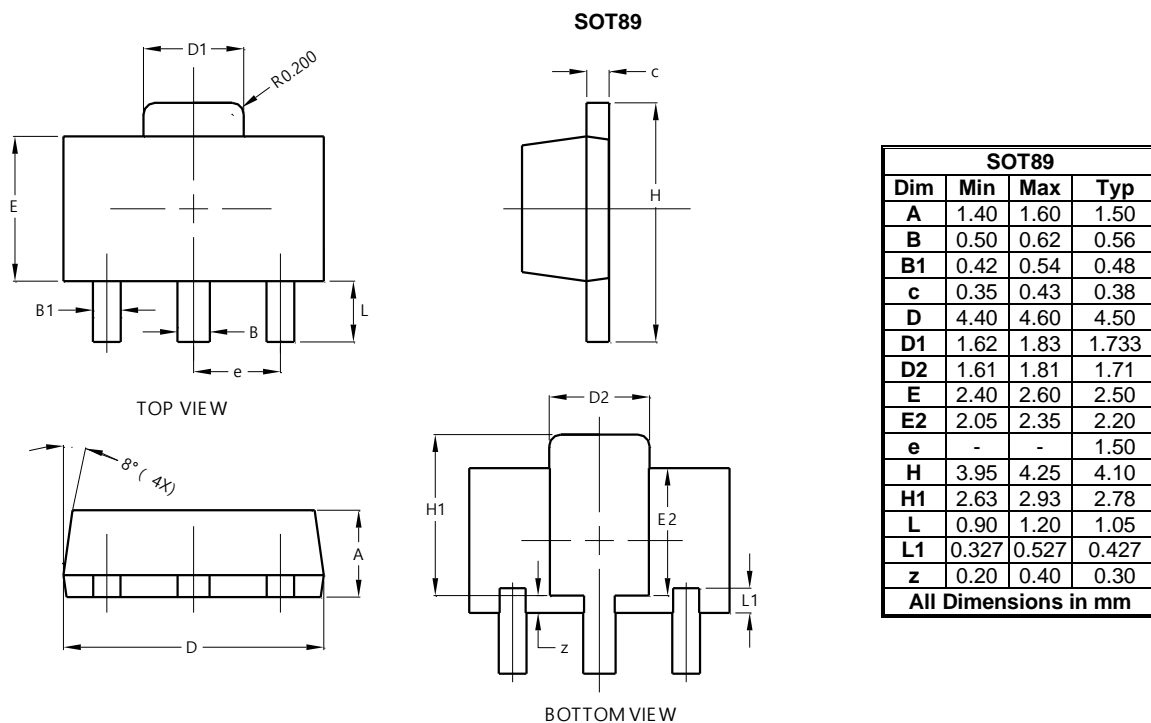


Figure 13. Transient Thermal Resistance

Package Outline Dimensions



Suggested Pad Layout

